

# 4N50

Power MOSFET

## 4 A, 500 V N-CHANNEL POWER MOSFET

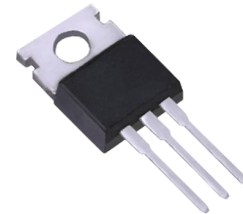
### ■ DESCRIPTION

The UTC **4N50** is an N-channel mode power MOSFET using UTC's advanced technology to provide customers with planar stripe and DMOS technology. This technology allows a minimum on-state resistance and superior switching performance. It also can withstand high energy pulse in the avalanche and commutation mode.

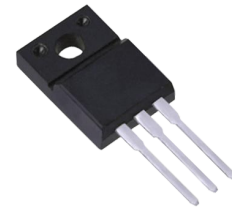
The UTC **4N50** is generally applied in high efficiency switch mode power supplies, active power factor correction and electronic lamp ballasts based on half bridge topology.

### ■ FEATURES

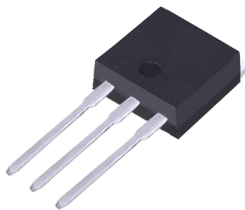
- \*  $I_D = 4A$
- \*  $V_{DS} = 500V$
- \*  $R_{DS(ON)} = 2.0\Omega @ V_{GS} = 10V$
- \* High Switching Speed
- \* 100% Avalanche Tested



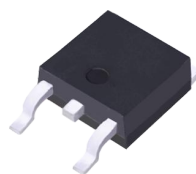
TO-220



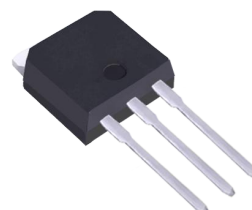
TO-220F



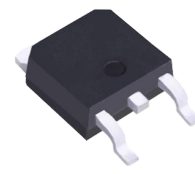
TO-262



TO-263



TO-251



TO-252

■ ABSOLUTE MAXIMUM RATINGS ( $T_C=25^\circ\text{C}$ , unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		$V_{DSS}$	500	V
Gate-Source Voltage		$V_{GSS}$	$\pm 30$	V
Drain Current	Continuous ( $T_C=25^\circ\text{C}$ )	$I_D$	4	A
	Pulsed (Note 3)	$I_{DM}$	16 (Note 2)	A
Avalanche Current (Note 3)		$I_{AR}$	4	A
Avalanche Energy	Single Pulsed (Note 4)	$E_{AS}$	216	mJ
	Repetitive (Note 3)	$E_{AR}$	8.5	mJ
Peak Diode Recovery $dv/dt$ (Note 5)		$dv/dt$	4.5	V/ns
Power Dissipation	TO-220	$P_D$	85	W
	TO-220F		28	
	TO-251/TO-252		52	
Derate above $25^\circ\text{C}$	TO-220		0.67	W/ $^\circ\text{C}$
	TO-220F		0.22	
	TO-251/TO-252		0.41	
Junction Temperature		$T_J$	+150	$^\circ\text{C}$
Storage Temperature		$T_{STG}$	-55~+150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Drain current limited by maximum junction temperature
3. Repetitive Rating: Pulse width limited by maximum junction temperature
4.  $L = 27\text{mH}$ ,  $I_{AS} = 4\text{A}$ ,  $V_{DD} = 50\text{V}$ ,  $R_G = 25\Omega$ , Starting  $T_J = 25^\circ\text{C}$
5.  $I_{SD} \leq 4\text{A}$ ,  $di/dt \leq 200\text{A}/\mu\text{s}$ ,  $V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220	$\theta_{JA}$	62.5	$^\circ\text{C}/\text{W}$
	TO-220F		62.5	
	TO-251/TO-252		110	
Junction to Case	TO-220	$\theta_{JC}$	1.47	$^\circ\text{C}/\text{W}$
	TO-220F		4.5	
	TO-251/TO-252		2.4	

■ ELECTRICAL CHARACTERISTICS ( $T_c=25^\circ\text{C}$ , unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
<b>OFF CHARACTERISTICS</b>							
Drain-Source Breakdown Voltage	$BV_{DSS}$	$I_D=250\mu\text{A}$ , $V_{GS}=0\text{V}$	500			V	
Drain-Source Leakage Current	$I_{DSS}$	$V_{DS}=500\text{V}$ , $V_{GS}=0\text{V}$			25	$\mu\text{A}$	
Gate- Source Leakage Current	Forward	$I_{GSS}$			+100	nA	
	Reverse				-100	nA	
<b>ON CHARACTERISTICS</b>							
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}$ , $I_D=250\mu\text{A}$	2.0		4.0	V	
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10\text{V}$ , $I_D=2\text{A}$		1.6	2.2	$\Omega$	
<b>DYNAMIC PARAMETERS</b>							
Input Capacitance	$C_{ISS}$	$V_{GS}=0\text{V}$ , $V_{DS}=25\text{V}$ , $f=1.0\text{MHz}$		485	650	pF	
Output Capacitance	$C_{OSS}$				65	90	pF
Reverse Transfer Capacitance	$C_{RSS}$				5	8	pF
<b>SWITCHING PARAMETERS</b>							
Total Gate Charge	$Q_G$	$V_{GS}=10\text{V}$ , $V_{DS}=400\text{V}$ , $I_D=4\text{A}$ (Note 1, 2)		11	15	nC	
Gate to Source Charge	$Q_{GS}$				3		nC
Gate to Drain Charge	$Q_{GD}$				5		nC
Turn-ON Delay Time	$t_{D(ON)}$	$V_{DD}=250\text{V}$ , $I_D=4\text{A}$ , $R_G=25\Omega$ (Note 1, 2)		14	38	ns	
Rise Time	$t_R$				21	52	ns
Turn-OFF Delay Time	$t_{D(OFF)}$				27	64	ns
Fall-Time	$t_F$				20	50	ns
<b>SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS</b>							
Maximum Body-Diode Continuous Current	$I_S$				4	A	
Maximum Body-Diode Pulsed Current	$I_{SM}$				16	A	
Drain-Source Diode Forward Voltage	$V_{SD}$	$I_S=4\text{A}$ , $V_{GS}=0\text{V}$			1.6	V	
Body Diode Reverse Recovery Time	$t_{RR}$	$I_S=4\text{A}$ , $V_{GS}=0\text{V}$ , $di_F/dt=100\text{A}/\mu\text{s}$ (Note 1)		350		ns	
Body Diode Reverse Recovery Charge	$Q_{RR}$				33		$\mu\text{C}$

- Notes: 1. Pulse Test: Pulse width  $\leq 300\mu\text{s}$ , Duty cycle  $\leq 2\%$   
 2. Essentially independent of operating temperature

### ■ TYPICAL CHARACTERISTICS

